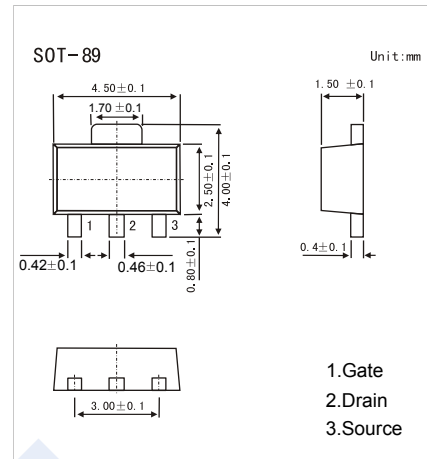


## P-Channel MOSFET

### 2SJ288

#### ■ Features

- $V_{DS} (V) = -60V$
- $I_D = -0.5 A$
- $R_{DS(ON)} < 3 \Omega$  ( $V_{GS} = -10V$ )
- $R_{DS(ON)} < 4 \Omega$  ( $V_{GS} = -4V$ )



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DS}$	-60	V	
Gate-Source Voltage	$V_{GS}$	$\pm 15$		
Continuous Drain Current	$I_D$	-0.5	A	
Pulsed Drain Current (Note.1)	$I_{DM}$	-2		
Power Dissipation	$P_D$	$T_c = 25^\circ C$	3.5	W
			1.3	
Junction Temperature	$T_J$	150	$^\circ C$	
Junction Storage Temperature Range	$T_{stg}$	-55 to 150		

Note.1:  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$

#### ■ Electrical Characteristics $T_a = 25^\circ C$

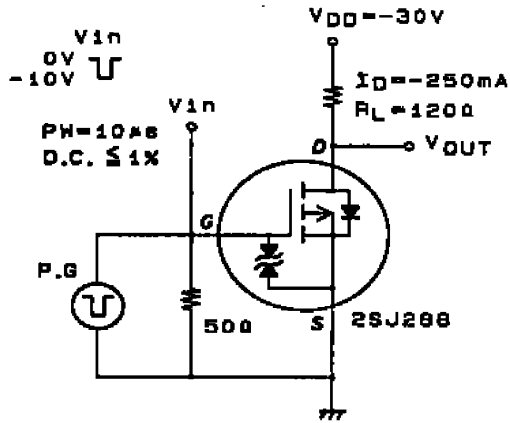
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -1mA, V_{GS} = 0V$	-60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60V, V_{GS} = 0V$			-100	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 12V$			$\pm 10$	$\mu A$
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -10V, I_D = -1mA$	-1		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -250mA$			3	$\Omega$
		$V_{GS} = -4V, I_D = -250mA$			4	
Forward Transconductance	$g_{FS}$	$V_{DS} = -10V, I_D = -250mA$	240	400		mS
Input Capacitance	$C_{iss}$	See Specified Test circuit		45		pF
Output Capacitance	$C_{oss}$			20		
Reverse Transfer Capacitance	$C_{rss}$			5		
Turn-On DelayTime	$t_{d(on)}$			7		
Turn-On Rise Time	$t_r$			10	ns	
Turn-Off DelayTime	$t_{d(off)}$			35		
Turn-Off Fall Time	$t_f$			20		
Diode Forward Voltage	$V_{SD}$	$I_S = -0.5A, V_{GS} = 0V$		-1		V

#### ■ Marking

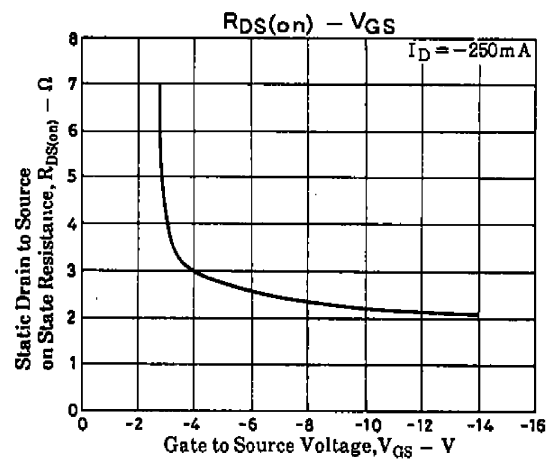
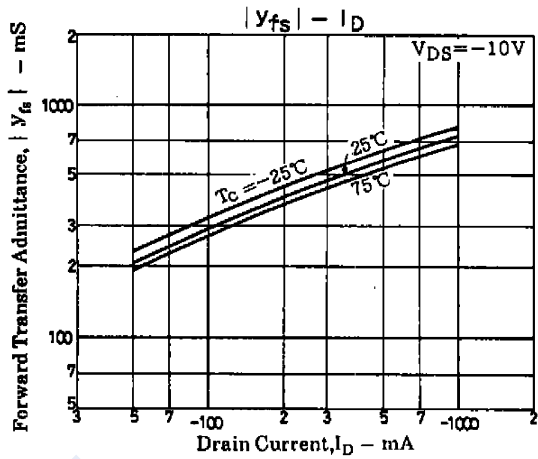
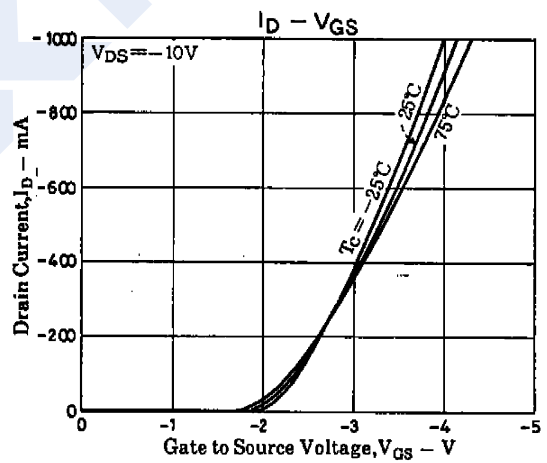
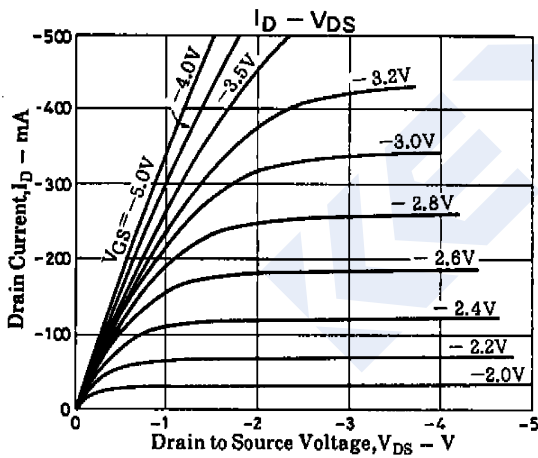
Marking	JE
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## P-Channel MOSFET 2SJ288

### Switching Time Test Circuit



■ Typical Characteristics



## P-Channel MOSFET 2SJ288

■ Typical Characteristics

